Disorder effects in topological insulator nanowires

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(Dated: July 7, 2021)

Three-dimensional topological insulator (TI) nanowires with quantized surface subband spectra are studied as a main component of Majorana bound states (MBS) devices. However, such wires are known to have large concentration $N \sim 10^{19} \text{cm}^{-3}$ of Coulomb impurities. It is believed that a MBS device can function only if the amplitude of long-range fluctuations of the random Coulomb potential $\Gamma$ is smaller than the subband gap $\Delta$. Here we calculate $\Gamma$ for recently experimentally studied large-dielectric-constant (Bi$_{1-x}$Sb$_x$)$_2$Te$_3$ wires in a small-dielectric-constant environment (no superconductor). We show that provided by such a dielectric-constant contrast, the confinement of electric field of impurities within the wire allows more distant impurities to contribute into $\Gamma$, leading to $\Gamma \sim 3\Delta$. We also calculate a TI wire resistance as a function of the Fermi level and carrier concentration due to scattering on Coulomb and neutral impurities, and do not find observable discrete subband-spectrum related oscillations at $N \gtrsim 10^{18} \text{cm}^{-3}$.

I. INTRODUCTION

Topological insulator (TI) attracts strong attention because of their conducting surface states. TI nanowires are predicted to host Majorana bound states (MBS) on their ends [1–6]. Here we study the role of Coulomb impurities in TI nanowires.

Typically, as-grown TI crystals are heavily doped semiconductors with concentration of donors $N \sim 10^{19} \text{cm}^{-3}$. (For certainty, we talk about n-type case where the Fermi level $E_F$ is high in the conduction band). However, to make the bulk insulating and employ the surface states in transport, one has to move the Fermi level close to the Dirac point. This is done by intentional compensation of donors with an almost equal concentration of acceptors.

This seemingly easy solution of the Fermi-level problem, however, comes with a price [7]. In fully compensated TI, all donors and acceptors are charged, and these randomly distributed charges in space create random potential fluctuations as large as the TI bulk semiconductor gap. These fluctuations create equal numbers of electron and hole puddles, and substantially reduce the activation energy of the bulk transport [7–9]. At the same time near the surface, the random potential of charged impurities smears the Dirac point by the energy $\Gamma$ self-consistently determined by the surface electrons (holes) screening [10, 11]. This smearing was observed by the scanning tunnel microscopy [12].

Similar Dirac point smearing by disorder happens in thin TI films sandwiched between two low-dielectric-constant layers [13], where the Rytova-Chaplik-Entin-Keldysh modification [14–16] of the Coulomb potential of a charged impurity slows down the potential decay in space, and allows a larger number of the film impurities to contribute to $\Gamma$.

Recently, substantial experimental progresses has been made in thin TI nanowires and nanoribbons, where all mobile electrons (holes) are located at the wire sufrace [17–27]. They attract attention because the Dirac spectrum of surface electrons (holes) splits in equidistant surface subbands separated by the substantial gap $\Delta$ due to the small wire cross-section perimeter. In such a TI wire, one can realize MBS with the help of superconductor proximity effect, if one is able to keep the Fermi level within a certain, say the first, subband in the whole length of the TI wire [6]. For such a fine tuning, the subband gap $\Delta$ should be bigger than the amplitude $\Gamma$ of fluctuations of the long-range electrostatic potential along the wire due to charged impurities. In this case the resistance $R(E_F)$ should oscillate with the Fermi level $E_F$. Reference [20] claims small resistance oscillations in TI wires of radius $a = 20 \text{nm}$ on relatively thick silicon oxide substrate separating it from the heavily doped Si gate in the absence of any superconductor. These oscillations seemingly indicate that $\Gamma \lesssim \Delta$.

In this paper we calculate $\Gamma$ for a cylindrical TI wire of the radius $a$ with concentration $N$ of Coulomb impurities in the set up of Ref. [20]. To this end we study the self-consistent screening of Coulomb impurities by surface electrons and holes, in a way similar to Refs. [10, 13]. We show that $\Gamma \sim 3\Delta$ for $N \sim 10^{19} \text{cm}^{-3}$. We also calculate a TI wire resistance $R(E_F)$ due to scattering on the Coulomb and short-range impurities and find no observable oscillation at $N \gtrsim 10^{18} \text{cm}^{-3}$ because $\Gamma \gtrsim \Delta$.

Our results may seem counter intuitive. One might think that the role of disorder in a thin TI wire should be smaller than in the bulk TI or in a TI film. Indeed, at a given 3D concentration of charged impurities $N$, the 1D concentration of them $N_1 = N/a^2$ in a thin TI wire is quite small, so that there are less impurities at a given distance $r > a$ from an observation point in this case. We, however, show that this larger-distance effect is compensated by the effect of confinement of the electric field inside the TI wire due to its large dielectric constant $\kappa \sim 200$. As a result, the Coulomb potential of each impurity slowly decays along a wire. This allows larger number of Coulomb impurities to contribute to $\Gamma$.

The plan of this paper is as follows. In Sec. II we calculate the amplitude $\Gamma$ of long-range potential fluctuations produced by randomly positioned Coulomb impurities inside the wire. In Sec. III we calculate a TI wire resistance limited by the scattering of surface electrons on $N$ charged impurities. In Sec. IV we calculate additional contribution to the resistance from located at the surface point-like neutral impurities. We
II. SELF-CONSISTENT CALCULATION OF DISORDER POTENTIAL

Consider the Coulomb interaction inside an infinitely long wire \((L_x \rightarrow \infty)\) of radius \(a\) with dielectric constant \(\kappa\) surrounded by a dielectric environment with dielectric constant \(\kappa_e\) such that \(\kappa \gg \kappa_e\). (See Fig. 1). The electrostatics of this problem for a topologically trivial wire (no surface electrons or holes) was solved and used in Refs. [28–32], and below we summarize their results. Due to big dielectric-constant mismatch, the electric field lines of a point charge are trapped inside the wire for a long distance \(\xi \gg a\) before exiting outside. Here the characteristic length \(\xi\) is determined by the equation

\[
\xi^2 = \frac{a^2}{\kappa} \ln(2\xi/a).
\]

The Fourier transform of Eq. (2) is given by

\[
v_0(q) = \int_{-\infty}^{\infty} dx \ v_0(x) e^{-iqx} = \frac{2\epsilon E_0}{q^2 + \xi^2},
\]

where \(q < a^{-1}\) since \(|x| > a\).

In the absence of free electrons (holes) screening, Eq. (2) leads to the amplitude of potential fluctuations of charged impurities \(\sim \epsilon E_0 \sqrt{N/a^2} \xi\). For highly compensated (Bi_{1-x}Sb_{y}Te_{3}) (BST) nanowires used in experiments [20] with \(a = 20\) nm, and \(N = 10^{19}\) cm\(^{-3}\), \(\kappa = 200\) [33–35], \(\kappa_e = 2.5\) (average of the vacuum \(\kappa_1 = 1\) and silicon oxide values \(\kappa_2 = 4\)), we have \(\xi = 11a\) and this potential fluctuation is of order 0.4 eV.

To describe the screening by surface Dirac electrons and holes, we start from the equation for the electric potential of screened charged impurities \(\phi(x)\)

\[
\mu[\lambda(x)] - e\phi(x) = E_F,
\]

where \(E_F\) is the (gate tuned) Fermi level (electro-chemical potential), \(\mu[\lambda(x)]\) is the (local) chemical potential, and \(-e\lambda(x)\) is the (local) linear charge density of carriers. Explicitly, we can calculate \(\lambda\) as a function of \(\mu\) through

\[
\lambda(\mu) = \frac{\text{sgn}(\mu)}{L_x} \sum_{k,l} \Theta(\mu^2 - \epsilon_i^2(k))
\]

\[
= \frac{\text{sgn}(|\mu|)}{\pi \hbar v_F} \sum_i \Theta(\mu^2 - \epsilon_i^2) \sqrt{\mu^2 - \epsilon_i^2},
\]

where \(\text{sgn}(\mu)\) is the sign function, \(\Theta(x)\) is the Heaviside theta function, and the energy spectrum for Dirac electrons is given by

\[
\epsilon_i(k) = \hbar v_F \sqrt{k^2 + (l/a)^2},
\]

dirac holes spectrum is \(-\epsilon_i(k)\). Here \(v_F\) is the Fermi velocity, \(k\) is the momentum along wire, and \(l = \pm 1/2, \pm 3/2, \ldots\) are angular momentum quantum number due to antiperiodic boundary condition. At \(k = 0\), neighboring subbands are separated by equidistance gap \(\Delta = \hbar v_F/a\). Here in Eq. (5) and below we abbreviate \(\epsilon_i(k) = 0\) as \(l|\Delta\) as \(\epsilon_i\) for convenience. In experiments with BST TI nanowires with radius \(a = 20\) nm [20], \(\Delta \sim 13\) meV which, as we will see below, is much smaller than the amplitude of fluctuations of screened Coulomb potential \(\Gamma \sim 35\) meV. Therefore, it is natural to consider the limit \(\mu^2 \gg \Delta^2\), such that the sum over \(l\) in Eq. (5) can be approximated by an integral and gives

\[
\lambda(\mu) = \frac{\text{sgn}(\mu)}{2} \left( \frac{\mu}{\hbar v_F} \right)^2,
\]

which is related to the 2D charge concentration of the wire surface \(n = \lambda/2\pi a = k_F^2/4\pi\), where \(k_F = \mu/\hbar v_F\) is the (local) 2D Fermi wave vector.

If \(E_F\) is large enough so that \(E_F^2 \gg \epsilon_i^2\), then \(\mu[\lambda(x)]\) can be linearized in the local charge concentration variation \(\delta \lambda(x)\)

\[
\mu[\lambda(x)] = E_F + \delta \lambda(x)/g(\mu),
\]

where \(g(\mu) = d\lambda/d\mu\) is the density of states (DOS) at zero temperature. Explicitly we have

\[
g(\mu) = \frac{\kappa \alpha |\mu|}{\pi \epsilon^2} \sum_i \Theta(\mu^2 - \epsilon_i^2) \sqrt{\mu^2 - \epsilon_i^2}
\]
where $\alpha = e^2/k_B T_F$ is the effective fine structure constant. In continuous limit $\mu^2 \gg \Delta^2$, the DOS has a simple expression

$$g(\mu) = \frac{|\mu|}{a^2 \Delta^2}, \quad (10)$$

which also reminds us the 2D DOS $\nu(\mu) = g(\mu)/2\pi a$.

In the Thomas-Fermi (TF) approximation, the dielectric function is given by

$$\epsilon(q) = 1 - v_0(q) \Pi_{TF}, \quad (11)$$

where the TF polarization bubble is $\Pi_{TF} = -g(\mu)$, and the bare interaction $v_0(q)$ is given by Eq. (3). We arrive at the screened potential of one charge impurity within a thin TI wire

$$v(q) = \frac{v_0(q)}{\epsilon(q)} = \frac{2eE_0}{q^2 + r_s^{-2}}, \quad (12)$$

where

$$r_s = \left[ \xi^{-2} + 2eE_0 g(\mu) \right]^{-1/2} \quad (13)$$

is the screening length and $q < a^{-1}$. In real space the screened potential

$$v(x) = eE_0 r_s e^{-|x|/r_s} \quad (14)$$

is similar to the bare potential Eq. (2), but with a different characteristic length $r_s < \xi$.

If impurities are randomly distributed inside the wire, the mean squared fluctuation of the potential is given by

$$\langle \phi^2 \rangle = \frac{1}{\epsilon^2} \int_{-\infty}^{\infty} dx \, v^2(x) N_\alpha a^2 = N_\alpha a^2 E_0 r_s^3. \quad (15)$$

In the rest of this section, we concentrate on the charge neutrality point where $E_N = 0$, and $\phi$ has the Gaussian distribution function with $\langle \phi \rangle = 0$ and $\langle \phi^2 \rangle = \Gamma^2/\epsilon^2$. Next we calculate the average density of states $\langle g \rangle$ using the Gaussian distribution function of $\phi$:

$$\langle g \rangle = \int_{-\infty}^{\infty} d(\epsilon \phi) g(\epsilon \phi) e^{-\epsilon^2 \phi^2/2\Gamma^2} \sqrt{2\pi \Gamma^2} = \frac{\kappa a}{\pi e^2} \sum_l \exp(-\epsilon^2 l/2\Gamma^2). \quad (16)$$

In the limit $\Gamma \gg \Delta$, the summation over $l$ can be replaced by an integral and we arrive at

$$\langle g \rangle = \sqrt{\frac{2}{\pi}} \frac{\Gamma}{a \Delta^2}. \quad (17)$$

Same result can be obtained if we average Eq. (10) directly [36]. Replacing $g(\mu)$ by $\langle g \rangle$ and ignoring the first term in Eq. (13) because as we will see $r_s \ll \xi$, we arrive at

$$r_s \approx \left[ 2eE_0 \langle g \rangle \right]^{-1/2} = \frac{a}{2} \left( \frac{\pi}{2} \right)^{1/4} \left( \frac{\Delta}{\alpha T} \right)^{1/2}. \quad (18)$$

Substituting this $r_s$ back into Eq. (15) and using $\Gamma^2 = e^2 \langle \phi^2 \rangle$, we can solve for $\Gamma$

$$\Gamma = \left( \frac{\pi}{2} \right)^{1/2} a^{1/7} (Na_\alpha^3)^{2/7} \Delta = \left( \frac{\pi}{2} \right)^{1/2} \frac{e^2}{\kappa a} (Na_\alpha^3)^{2/7}. \quad (19)$$

Using $a = 20$ nm, $\kappa = 200$, and $N = 10^{19}$ cm$^{-3}$, $v_F = 4 \times 10^5$ m/s [37], one gets $\alpha = 0.027$, $\Gamma = 35$ meV and $\Delta = 13$ meV. Thus, our assumption $\Gamma \gg \Delta$ is well justified. Note that according to Eq. (19) $\Gamma$ does not decrease with decreasing $a$ in spite of the decrease of linear concentration $\pi a^2 N$ of Coulomb impurities. This is a result of the confinement of electric field lines inside of a large-dielectric-constant TI wire described by Eq. (14), which allows more distant impurities to contribute in the amplitude of the disorder potential.

Substituting Eq. (19) back to Eq. (18), we have

$$r_s = \frac{a}{2} \alpha^{-2/7} (Na_\alpha^3)^{-1/7}. \quad (20)$$

The above theory assumes that $r_s > a$, so that the random potential depends only on $x$ and we can avoid averaging of random potential over perimeter of a wire cross-section. Indeed, for $N = 10^{19}$ cm$^{-3}$ and $a = 20$ nm, we get $r_s = 2.1a$, so that the above theory is (marginally) applicable. At the same time our assumption that $r_s \ll \xi = 11a$ is justified as well.

On the other hand, for $a > r_s$, i.e., $\alpha > a_\alpha = \alpha^{-2/3} N^{-1/3}$, one can neglect the curvature of the wire surface and our Eqs. (19) and (20) cross over to $\Gamma$ and $r_s$ for a bulk TI sample calculated in Ref. [10].

Above we ignored the concentration of charged impurities in the environment outside of the TI wire $N_e$. Let us now evaluate the role of such impurities, say in the silicon oxide. For a trivial wire to save electrostatic energy, the electric field lines of an impurity at distance $r < \xi$ from the wire surface first enter inside the wire and then spread inside the wire to the distance $\sim \xi$ before exiting outside the wire to infinity. Thus, one can think that effectively each outside impurity is represented inside the wire by a charge $e$ cylinder, with length $r$ and radius $a$. In the presence of surface screening of a TI wire, only small minority of the outside impurities with $r < r_s$ contribute in fluctuating charge of the volume $a^2 r_s$. As a result, total effective concentration of impurities projected from outside the wire is $N_e (r_s/a)^2$. If $N_e (r_s/a)^2 \ll N$, where $r_s$ is given by Eq. (20), then impurities outside the wire can be ignored. For example, for the BST TI wire with $N = 10^{19}$ cm$^{-3}$ and $a = 20$ nm on silicon oxide substrate with $38 N_e \sim 10^{17}$ cm$^{-3}$, using $r_s/a \sim 2$, we get $N_e (r_s/a)^2 \sim 4 \times 10^{17}$ cm$^{-3} \ll N$. Thus, our results are valid [39].

III. RESISTANCE DUE TO SCATTERING ON COULOMB IMPURITIES

In this section, we calculate the resistance $R$ as a function of the Fermi level $E_F$ limited by the scattering off charged impurities. Let us start with the conductivity of the TI wire surface. In the linear screening region $\mu^2 \gg e^2 \phi^2$, where the
carrier concentration is weakly perturbed by impurities, using Boltzmann kinetic equation for Dirac electrons (holes), one arrives at the surface conductivity [40],

\[
\sigma = \frac{e^2 |\mu|^2}{\hbar} \tau. \tag{21}
\]

Here \(\tau\) is the transport relaxation time whose inverse is given by

\[
\frac{1}{\tau} = \frac{2\pi}{\hbar} \sum_{i,f} w_i \left| |V_{fi}|^2 \right| \frac{1}{2} (1 - \cos^2 \theta) \delta(\varepsilon_f - \varepsilon_i). \tag{22}
\]

Here the subscripts \(f/i\) denote the final (initial) states with momentum \((k_f, l_f/a)\) or \((k_i, l_i/a)\), \(w_i = g_i/\hbar g\) is the probability to be initialized in state \(i\), where \(g_i(\mu) = (\pi a \Delta)^{-1}\Theta(\mu^2 - \varepsilon_i^2)|\mu|/\sqrt{\mu^2 - \varepsilon_i^2}\) is the DOS of the \(i\)th sub-band [c.f. Eq. (9)], and \(\ldots\) denotes the average over impurities position. The scattering angle \(\theta\) can be related to the (local) transfer momentum \(\mathbf{p} = (k_f - k_i, l_f/a - l_i/a)\) via

\[
\cos \theta = 1 - \frac{k^2}{2E^2},
\]

where \(k_r = \mu/\hbar v_F\). The extra factor \((1 + \cos \theta)/2\) in Eq. (23) arises when the back scattering is suppressed as a consequence of the spin texture at the Dirac point, as in graphene or Weyl semimetals [41, 42].

Because the long range Coulomb potential Eq. (14) is a function of \(x\) only, the angular momentum is conserved and we have

\[
\left| |V_{j'i'}| \right| = \delta_{j'i'} \frac{N \pi a^2}{L_x} |v(q)|^2, \tag{23}
\]

where \(L_x\) is the length of the wire and \(q = k_f - k_i\) is the momentum transfer along \(x\). Combining the angular momentum conservation with the energy conservation, there are only two possibilities for the final momentum \(k_f = \pm k_i\). However, only \(k_f = -k_i\) and \(l_f = l_i\) is allowed, because the scattering angle factor \((1 - \cos \theta)\) forbids the forward scattering \(k_f = k_i\) and \(l_f = l_i\). Therefore, using Eqs. (12), (22), and (23), we arrive at \(1/\tau\) contributed from the scattering on long-range potential:

\[
\frac{1}{\tau(\mu)} = \frac{1}{\tau_0(\mu)} f(\mu), \tag{24}
\]

where

\[
\frac{1}{\tau_0(\mu)} = \frac{16 N \alpha^2 \sigma^2 \Delta^3}{h \mu^2} \approx \frac{4 N \alpha^3 \Delta^4}{\hbar |\mu|^4}, \tag{25}
\]

(we used \(r_\mu(\mu) \approx a\sqrt{\Delta/4|\mu|}\) assuming \(r_\mu \ll \xi\) and the function

\[
f(\mu) = \frac{\alpha \Delta^2}{\mu^2} \sum_i \frac{\varepsilon_i^2}{\mu^2} \left[ \frac{\Theta(\mu^2 - \varepsilon_i^2)}{1 - \frac{\varepsilon_i^2}{\mu^2} + \frac{\Delta^2}{4\pi^2 \mu^2}} \right]. \tag{26}
\]

which oscillates around its average value \(f = 1\). Below we use Eq. (25) to study the monotonous dependence of the wire resistance on the Fermi energy \(E_F\).

Note that the right hand side of Eq. (25) is proportional to \(r_\mu^2\) because the main contribution to the scattering rate is at small momentum transfer \(q \sim r_\mu^{-1}\). Such an unconventional role of long range potential results from the electric field concentration in a wire which allows more distant Coulomb impurities to contribute into scattering [43].

At \(|E_F| \gg \Gamma\) and, therefore, \(|\mu| \simeq |E_F| \gg \Gamma\) we can substitute Eq. (25) into Eq. (21). Substituting \(E_F\) for \(\mu\) we obtain for the wire resistance \(R = \frac{L_x}{2\pi a}\)

\[
R(E_F) = \frac{h}{e^2} \frac{16 N \alpha^3 \Delta}{2\pi a}. \tag{27}
\]

At \(|E_F| \lesssim \Gamma\), screening becomes nonlinear and Eq. (27) saturates at \(\frac{R(E_F)}{\Gamma} \approx \Gamma\) and using Eq. (19) we obtain the maximum resistance

\[
R_{\text{max}} \approx \frac{h}{e^2} \frac{2^6 \alpha^3 \Gamma^7 L_x}{(N \alpha^3)^{1/7}}. \tag{28}
\]

Now let us compare Eqs. (27) and (28) with experiment [20]. Experimental resistance [20] has a maximum \(R_{\text{max}} \approx 50\, \Omega\) at the Dirac point, and slightly (by \(\sim 10\%\) decreases at \(|E_F|/\Delta \simeq 9/2\). For \(L_x = 1\, \mu\text{m}\), the radius \(a = 20\, \text{nm}\), and \(N = 10^{19}\, \text{cm}^{-3}\), Eq. (28) predicts \(R_{\text{max}} \approx 150\, \Omega\). This maximum resistance is somewhat bigger than the experimental one [20]. Also, the theory of charged impurities predicts the resistance stays constant only for \(|E_F|/\Delta \lesssim \Gamma\) and then decreases \(\propto E_F^{-4}\) which disagrees with experiments.

These disagreements motivate us to explore in the next section whether addition of surface short-range impurities to the bulk Coulomb ones can improve the agreement with experiments.

IV. CONTRIBUTION OF SHORT RANGE IMPURITIES TO A TI WIRE RESISTANCE

The short range impurity has potential \(v(r) = u_0 \sum_j \delta^{(2)}(r - r_j)\) where \(r_j\) is the 2D position of an impurity on the TI surface. The corresponding matrix element is given by

\[
\left| |V_{j'i'}| \right| = \frac{n_i u_0^2}{2\pi a L_x}, \tag{29}
\]

where \(n_i\) is the 2D concentration of short range impurities on the wire surface. It leads to the scattering rate

\[
\frac{1}{\tau(\mu)} = \frac{n_i u_0^2}{2\pi a} g(\mu), \tag{30}
\]

Substituting Eq. (30) into Eq. (21), we arrive at the contribution of short-range impurities to the TI wire resistance

\[
R(\mu) = \frac{h}{e^2} \frac{2 n_i u_0^2 g(\mu)}{a |\mu|} \frac{L_x}{2\pi a}. \tag{31}
\]

In continuous limit \(\mu^2 \gg \Delta^2\), we replace \(g(\mu)\) by Eq. (10) and obtain the independent-on-\(E_F\) resistance

\[
R_0 = \frac{h}{e^2} \frac{2 n_i u_0^2 L_x}{a^2 |\mu|^2}. \tag{32}
\]
It was shown [20] that on the top of the above classical behavior quantum oscillations of the density of states \( g(\mu) \) [see Eq. (9)] result in resistance oscillations as a function of the Fermi level with period \( \Delta \). However, we show below that these oscillations are very small due to the smearing effect of Gaussian fluctuations of the long-range potential. For example, the amplitude of a harmonics with period \( \Delta \) is suppressed by a factor \( \exp[-2\pi^2 \Gamma^2(E_F)/\Delta^2] \). The Fermi-level dependent \( \Gamma(E_F) \) can be obtained by substituting Eq. (13) into Eq. (15), assuming \( \xi \gg r_s \), and replacing all \( |\mu| \) by \( \sqrt{E_F^2 + 2\Gamma^2(E_F)/\pi} \):

\[
\Gamma(E_F) = \sqrt{\frac{\pi N a_0^3}{2}} \frac{a_1^{1/4} \Delta^{7/4}}{E_F^2 + 2\Gamma^2(E_F)/\pi^{3/8}}, \tag{33}
\]

Indeed, by solving for \( \Gamma = \Gamma(E_F = 0) \) self-consistently, we obtain the same expression \( \Gamma \) given by Eq. (19). At \( |E_F| \gg \Gamma \), one has \( \Gamma(E_F) \propto |E_F|^{-3/4} \).

As a result, we have the smeared density of states as a function of Fermi level

\[
\langle g(E_F) \rangle = \int_{-\infty}^{\infty} \dmu g(\mu) \frac{\exp\left[-(\mu - E_F)^2/2\Gamma^2(E_F)\right]}{\sqrt{2\pi \Gamma^2(E_F)}}, \tag{34}
\]

as shown in Fig. 2. Replacing \( g(\mu) \) by \( \langle g(E_F) \rangle \) in Equations (30) and (31), and replacing \( |\mu| \) by \( \sqrt{E_F^2 + 2\Gamma^2(E_F)^2/\pi} \) in Eq. (21), we get the wire resistance as a function of the Fermi level, as shown in Fig. 3.

The relatively weak dependence of TI wire resistance on \( E_F \) shown in Fig. 3 agrees with experiments [20]. However, small subband-related oscillations of the resistance seen in experiment show up in our theory only at \( N \) substantially smaller than \( 10^{18} \) cm\(^{-3}\).

In the above calculations we assumed the TI wire is in low-dielectric-constant environment without attached superconductors, and showed that at \( N = 10^{19} \) cm\(^{-3}\) the amplitude of potential fluctuations \( \Gamma \approx 3\Delta \). In fact, a future MBS device will contain superconductor stripe on the top of TI wire, which may substantially screen the potential and reduce \( \Gamma \).

Indeed, the superconductor stripe provides an image charge to each impurity inside the wire, and the resulting dipole potential at \( |x| > a \) is \( \sim e^2 a^2/\kappa |x|^3 \) and decays very fast. Therefore, we need to consider the contribution of impurities only at distances \( r \leq a \) from a surface observation point. They provide normal Coulomb potential because screening by surface electrons or holes at such small distances can be ignored. In the case \( Na^3 \gg 1 \) we have

\[
\Gamma^2 = \beta N a^3 (e^2/\kappa a)^2, \tag{35}
\]

where \( \beta \) is an unknown numerical coefficient which depends on geometries of the wire cross section and of adjacent superconductor. Similar result can be obtained by replacing \( r_s \) with \( a \) in Eq. (15). For \( N = 10^{19} \) cm\(^{-3}\), \( \kappa = 200 \), \( a = 20 \) nm, and for a not completely unreasonable \( \beta = 4\pi \), we get \( \Gamma = 12 \) meV, close to \( \Delta = 13 \) meV.

However, this \( \Gamma \) is not small enough for a MBS device, which has to keep chemical potential inside the same subband gap in order to avoid accidental Majorana pairs. For a long wire, even a single rare segment of the length \( 2a \) and of random potential amplitude larger than \( \Delta/2 \) is detrimental.

Let us estimate the probability of keeping the chemical po-
tential within the same gap along the whole wire. For that we divide the long wire into \( L_x/2a \) pieces with the length 2a each. For randomly positioned Coulomb impurities, the potential of each piece is an independent random variable following Gaussian distribution, and the probability for a single piece to fail is

\[
p = 1 - \int_{-\Delta/2}^{\Delta/2} du \frac{e^{-u^2/2\Gamma^2}}{\sqrt{2\pi}\Gamma} = \text{erfc}(\Delta/2\sqrt{2\Gamma}),
\]

where \( \text{erfc}(x) \) is the complementary error function. The probability for the whole wire to function is given by

\[
p_t = (1 - p)^{L_x/2a}.
\]

For example, in order to have \( p_t \geq 0.5 \) for a typical wire with \( L_x = 1 \) \( \mu m \) and \( a = 20 \) \( nm \) we need \( \Gamma/\Delta \leq 0.23 \) [44]. Using Eq. (35) with \( \beta = 4\tau \) we find necessary impurity concentration \( N \leq N_c = 7 \times 10^{17} \text{cm}^{-3} \).

To make disorder effects even weaker one can put MBS devices on high-dielectric-constant substrate, say insulating STO [17]. In this case, one can expect 50% yield of functioning MBS devices at a few times larger \( N_c \).

Thus, we find that necessary reduction of concentration of Coulomb impurities in TI nanowires for functioning MBS devices is similar to that in hybrid Rashba nanowires [45]. In both cases concentration of Coulomb impurities should be reduced at least by 10 times.

**ACKNOWLEDGMENTS**

We are grateful to Y. Ando, A. Kamenev, H. Legg, V. Pribiag, A. Rosch, and B. Skinner for reading the manuscript and useful comments. Y.H. was partially supported by the William I. Fine Theoretical Physics Institute.

In the opposite limit $\Gamma \ll \Delta$, the average DOS is exponentially suppressed by the gap and leads to $\langle g \rangle = (2\kappa \alpha/\pi e^2) e^{-\Delta^2/8\Gamma^2}$.

On the other hand, if $N_e (r_s/a)^2 > N$ the screening length $r_s$ should be recalculated self-consistently together with $\Gamma$. Then, instead of Eqs. (19) and (20), we arrive at new results $\Gamma \sim \Delta \alpha^{-1/9} (N_e a^3)^{2/9}$ and $r_s \sim a \alpha^{-4/9} (N_e a^3)^{-1/9}$.

Using $r_s(\mu) \approx a \sqrt{\Delta/4|\mu|}$, we have $r_s > a$ if $|\mu| < 9\Delta$ which covers most of the range of interest in experiments.

In this case Eq. (36) gives $p = 0.03 \ll 1$, so that Eq. (37) can be written as $p_t = \exp(-p L_s/2a)$.